

Diodes

Switching diodes

Type	Fig. Nr.	Maximum ratings			Characteristics								Notes
		I_V at $I_{amb} = 45^\circ\text{C}$ mW	I_F mA	U_R V	R_{thJA} °C/W	U_F at V	I_F mA	C_D at pF	U_R V	r_f at Ω	I_F mA	t_{rr} μs	
BA 173	1		300	300	≤ 450	≤ 1	100	≤ 2	150			0,35 ¹⁾	Clamping diode
BA 176	1					≤ 1,5	400						Aerial protection diode ²⁾
BA 178	3		100	35	≤ 400	≤ 1,2	100	≤ 1,3	30	≤ 1,3	5		RF switching diode
BA 182	3		100	35	≤ 400	≤ 1,2	100	≤ 1	20	≤ 0,7	5		RF switching diode
BA 243	2		100	20	≤ 350	≤ 1	100	≤ 2	15	≤ 1	10		RF switching diode
BA 244	2		100	20	≤ 350	≤ 1	100	≤ 2	15	≤ 0,5	10		RF switching diode
BAW 24	2	440	600	40	≤ 350	≤ 1,2	200	≤ 4	0			0,006 ³⁾	
BAW 25	2	440	600	40	≤ 350	≤ 1	200	≤ 4	0			0,006 ³⁾	
BAW 26	2	440	600	60	≤ 350	≤ 1,2	200	≤ 4	0			0,006 ³⁾	
BAW 27	2	440	600	60	≤ 350	≤ 1,25	400	≤ 4	0			0,006 ³⁾	
BAY 68	2	440	115	25	≤ 350	≤ 1	100	≤ 5	0			0,01 ¹⁾	
BAY 69	2	440	115	50	≤ 350	≤ 1	100	≤ 5	0			0,01 ¹⁾	
BAY 92	1	230 ⁴⁾	100	600	≤ 450	≤ 1	100	≤ 4	10			0,35 ¹⁾	
BAY 93	2	440	115	20	≤ 350	≤ 1	10	≤ 5	0			0,015 ¹⁾	
1N 4148 ○	2	440	200	75	≤ 350	≤ 1	10	≤ 4	0			0,008 ¹⁾	
1N 4149	2	440	200	75	≤ 350	≤ 1	10	≤ 2	0			0,008 ¹⁾	
1N 4151 ○	2	440	200	50	≤ 350	≤ 1	50	≤ 2	0			0,004 ¹⁾	
1N 4154	2	440	200	25	≤ 350	≤ 1	30	≤ 4	0			0,004 ¹⁾	
1N 4446 ○	2	440	200	75	≤ 350	≤ 1	20	≤ 4	0			0,008 ¹⁾	
1N 4447	2	440	200	75	≤ 350	≤ 1	20	≤ 2	0			0,008 ¹⁾	
1N 4448 ○	2	440	200	75	≤ 350	≤ 1	100	≤ 4	0			0,008 ¹⁾	
1N 4449	2	440	200	75	≤ 350	≤ 1	30	≤ 2	0			0,008 ¹⁾	

Remarks: ¹⁾ $I_F = I_R = 10\text{ mA}$, $i_R = 1\text{ mA}$; ²⁾ $I_R = 1\text{ }\mu\text{A}$, $U_{(BR)} = 100\text{ V}$, $\frac{I_P}{T} = 0,01$, $t_P = 0,3\text{ ms}$; ³⁾ $I_F = I_R = 10\text{...}100\text{ mA}$, $i_R = 0,1\text{ I}_R$; ⁴⁾ at $t_{amb} = 25^\circ\text{C}$

Data book reference: B 2 B ○ Can be delivered as "Qualified semiconductor device"

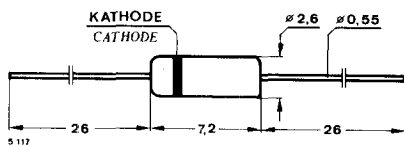


Fig. 1: 51 A 2 DIN 41 880
JEDEC DO 7

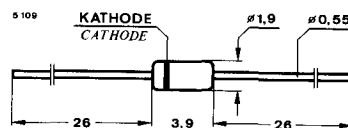


Fig. 2: 54 A 2 DIN 41 880
JEDEC DO 35

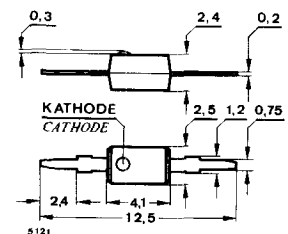


Fig. 3: Plastic case
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